Vishay Semiconductors

# Fast Recovery Diodes (Stud Version), 40 A, 70 A, 85 A



DO-5 (DO-203AB)

PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	40 A, 70 A, 85 A				
Package	DO-5 (DO-203AB)				
Circuit Configuration	Single				

#### **FEATURES**

- Short reverse recovery time
- · Low stored charge
- · Wide current range
- Excellent surge capabilities
- Stud cathode and stud anode versions
- Types up to 100 V<sub>RRM</sub>
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- DC power supplies
- Inverters
- Converters
- Choppers
- Ultrasonic systems
- Freewheeling diodes

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER TEST CONDITIONS		40HFL	70HFL	85HFL	UNITS		
1		40	70	85	Α		
I <sub>F(AV)</sub>	T <sub>C</sub> maximum	85	85	85	°C		
ı	50 Hz 400		700	1100	Α		
IFSM	60 Hz	420	730	1151	A		
I <sup>2</sup> t	50 Hz	800	2450	6050	A <sup>2</sup> s		
1-1	60 Hz	730	2240	5523			
I <sup>2</sup> √t		11 300	34 650	85 560	l <sup>2</sup> √s		
V <sub>RRM</sub>	Range	100 to 1000	100 to 1000	100 to 1000	V		
t <sub>rr</sub>		See Recovery Characteristics table	See Recovery Characteristics table	See Recovery Characteristics table	ns		
TJ	Range	-40 to +125	-40 to +125	-40 to +125	°C		

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#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS						
TYPE NUMBER (1)	V <sub>RRM</sub> , MAXIMUM PEAK REPETITIVE REVERSE VOLTAGE	V <sub>RSM</sub> , MAXIMUM PEAK NON-REPETITIVE REVERSE VOLTAGE	I <sub>FM</sub> , MAXIMUM PEAK REVERSE CURRENT AT RATED V <sub>RRM</sub> mA			
	T <sub>J</sub> = - 40 °C TO 125 °C V	T <sub>J</sub> = 25 °C TO 125 °C V	T <sub>J</sub> = 25 °C	$T_J$ = 125 °C		
VS-40HFL10S02, VS-40HFL10S05	100	150				
VS-40HFL20S02, VS-40HFL20S05	200	300				
VS-40HFL40S02, VS-40HFL40S05	400	500	0.1	10		
VS-40HFL60S02, VS-40HFL60S05	600	700	0.1	10		
VS-40HFL80S05	800	900				
VS-40HFL100S05	1000	1100				
VS-70HFL10S02, VS-70HFL10S05	100	150				
VS-70HFL20S02, VS-70HFL20S05	200	300				
VS-70HFL40S02, VS-70HFL40S05	400	500	0.1	15		
VS-70HFL60S02, VS-70HFL60S05	600	700	0.1	15		
VS-70HFL80S05	800	900				
VS-70HFL100S05	1000	1100				
VS-85HFL10S02, VS-85HFL10S05	100	150				
VS-85HFL20S02, VS-85HFL20S05	200	300				
VS-85HFL40S02, VS-85HFL40S05	400	500	0.1	00		
VS-85HFL60S02, VS-85HFL60S05	600	700	0.1	20		
VS-85HFL80S05	800	900				
VS-85HFL100S05	1000	1100				

#### Note

<sup>(1)</sup> Types listed are cathode case, for anode case add "R" to code, i.e. 40HFLR20S02, 85HFLR100S05 etc.

FORWARD CONDUCTION							
PARAMETER	SYMBOL	BOL TEST CONDITIONS			70HFL	85HFL	UNITS
Maximum average forward current at maximum case temperature	I <sub>F(AV)</sub>	180° conduction, half sine wave		40	70 75	85	A °C
Maximum RMS forward current	I <sub>F(RMS)</sub>			63	110	134	A
Maximum peak repetitive forward current	I <sub>FRM</sub>	Sinusoidal ha	alf wave, 30° conduction	220	380	470	Α
		t = 10 ms	Sinusoidal half wave, 100	400	700	1100	A
Maximum peak, one-cycle	I <sub>FSM</sub>	t = 8.3 ms	% $V_{RRM}$ reapplied, initial $T_J = T_J$ maximum	420	730	1151	
non-repetitive forward current		t = 10 ms	Sinusoidal half wave, no voltage reapplied, initial $T_J = T_J$ maximum	475	830	1308	
		t = 8.3 ms		500	870	1369	
		t = 10 ms	100 % V <sub>RRM</sub> reapplied, initial T <sub>J</sub> = T <sub>J</sub> maximum No voltage reapplied,	800	2450	6050	A <sup>2</sup> s
Maximum 124 for fusing	I <sup>2</sup> t	t = 8.3 ms		730	2240	5523	
Maximum I <sup>2</sup> t for fusing	141	t = 10 ms		1130	3460	8556	
		t = 8.3 ms	initial $T_J = T_J$ maximum	1030	3160	7810	
Maximum I <sup>2</sup> √t for fusing <sup>(1)</sup>	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied		11 300	34 650	85 560	A²√s
Maximum value of threshold voltage	V <sub>F(TO)</sub>	O) T <sub>J</sub> = 125 °C		1.081	1.085	1.128	V
Maximum value of forward slope resistance	r <sub>F</sub>			6.33	3.40	2.11	mΩ
Maximum forward voltage drop	$V_{FM}$	$T_J = 25  ^{\circ}\text{C},  I_{\text{FM}} = \pi  \text{x}  I_{\text{F(AV)}}$		1.95	1.85	1.75	V

#### Note

 $^{(1)}~I^2t$  for time  $t_x=I^2\sqrt{t}~x~\sqrt{t}_x$ 

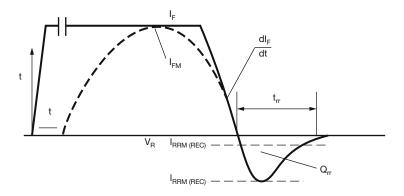
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RECOVERY CHARACTERISTICS										
PARAMETER	SYMBOL	TEST CONDITIONS	40HFL		70HFL		85HFL		UNITS	
FANAMETER	STWIDOL	TEST CONDITIONS	S02	S05	S02	S05	S02	S05	UNITS	
Typical reverse recovery time	+	$T_J$ = 25 °C, $I_F$ = 1 A to $V_R$ = 30 V, $dI_F/dt$ = 100 A/ $\mu$ s	70	180	60	150	50	120	ns	
Typical reverse recovery time t <sub>rr</sub>	$T_J = 25$ °C, - $dI_F/dt = 25$ A/ $\mu$ s, $I_{FM} = \pi$ x rated $I_{F(AV)}$	200	500	200	500	200	500	115		
Typical reverse recovered charge (		$T_J$ = 25 °C, $I_F$ = 1 A to $V_R$ = 30 V, $dI_F/dt$ = 100 A/ $\mu$ s	160	750	90	500	70	340	nC	
Typical reverse recovered charge	Q <sub>rr</sub>	$T_J = 25$ °C, - $dI_F/dt = 25$ A/ $\mu$ s, $I_{FM} = \pi \times rated I_{F(AV)}$	240	1300	240	1300	240	1300	110	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	40HFL	70HFL	85HFL	UNITS
Junction operating temperature range	TJ			-40 to 125		°C
Storage temperature range	T <sub>Stg</sub>		-40 to 150		30	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.60 0.36 0.30		- K/W	
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.25			
		Not lubricated thread, tighting on nut (1)		3.4 (30)		
Maximum allowable mounting torque		Lubricated thread, tighting on nut (1)	2.3 (20)		N·m	
(+ 0 %, - 10 %)		Not lubricated thread, tighting on hexagon (2)		4.2 (37)		(lbf · in)
		Lubricated thread, tighting on hexagon (2)	3.2 (28)			
Approximate weight				25		
Approximate weight				0.88		
Case style		JEDEC®		DO-5 (DO	D-203AB)	

#### Notes

- (1) Recommended for pass-through holes
- (2) Recommended for holed threaded heatsinks



 $\mathbf{I}_{\mathrm{F}},\,\mathbf{I}_{\mathrm{FM}}$  - Peak forward current prior to commulation

-dl<sub>E</sub>/dt - Rate of fail forward current

I<sub>RRM</sub> (REC) - Peak reverse recovery current

 $\mathbf{t}_{\mathrm{rr}}\,$  - Reverse recovery time

Q<sub>rr</sub> - Reverse recovered charge

Fig. 1 - Reverse Recovery Time Test Waveform

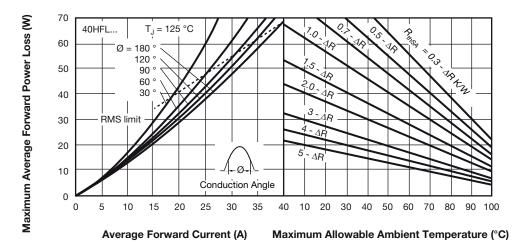


Fig. 2 - Current Rating Nomogram (Sinusoidal Waveforms), 40HFL Series

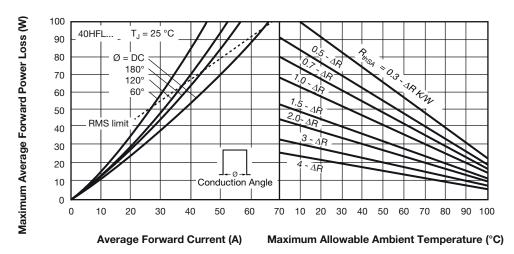
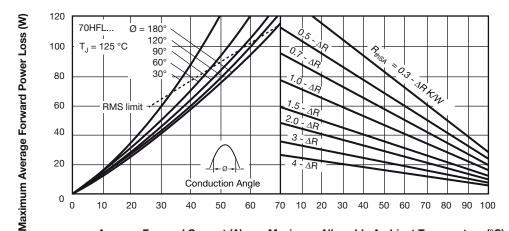


Fig. 3 - Current Rating Nomogram (Rectangular Waveforms), 40HFL Series



Average Forward Current (A) Maximum Allowable Ambient Temperature (°C) Fig. 4 - Current Rating Nomogram (Sinusoidal Waveforms), 70HFL Series

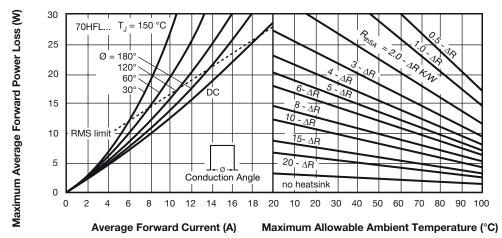
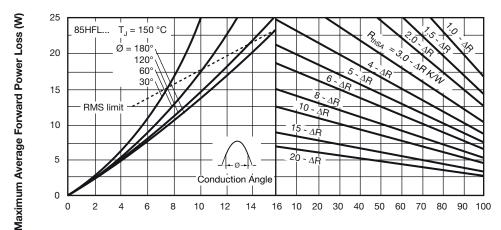


Fig. 5 - Current Rating Nomogram (Rectangular Waveforms), 70HFL Series



Average Forward Current (A) Maximum Allowable Ambient Temperature (°C) Fig. 6 - Current Rating Nomogram (Sinusoidal Waveforms), 85HFL Series

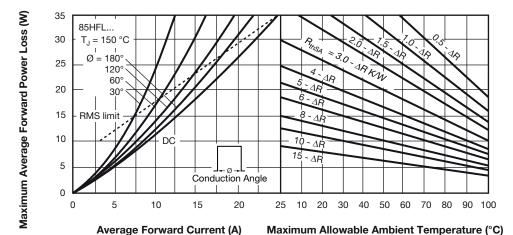


Fig. 7 - Current Rating Nomogram (Rectangular Waveforms), 85HFL Series

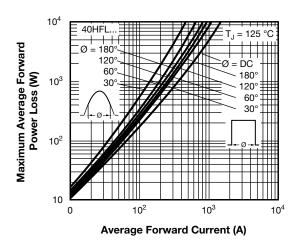


Fig. 8 - Maximum High Level Forward Power Loss vs. Average Forward Current, 40HFL Series

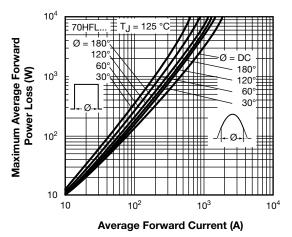


Fig. 9 - Maximum High Level Forward Power Loss vs. Average Forward Current, 70HFL Series

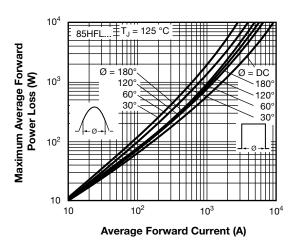


Fig. 10 - Maximum High Level Forward Power Loss vs. Average Forward Current, 85HFL Series

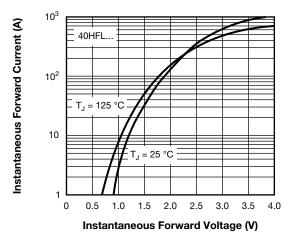


Fig. 11 - Maximum Forward Voltage vs. Forward Current, 40HFL Series

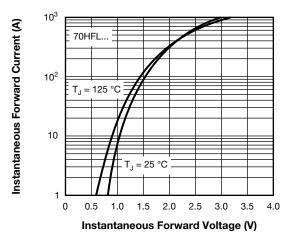


Fig. 12 - Maximum Forward Voltage vs. Forward Current, 70HFL Series

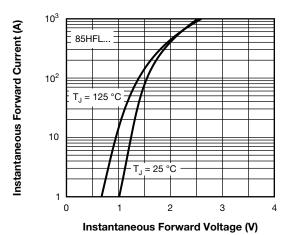


Fig. 13 - Maximum Forward Voltage vs. Forward Current, 85HFL Series

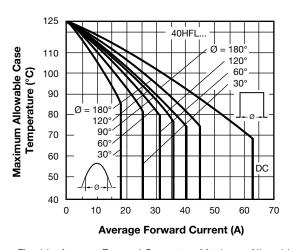


Fig. 14 - Average Forward Current vs. Maximum Allowable Case Temperature, 40HFL Series

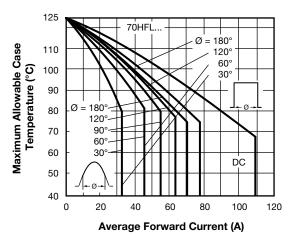


Fig. 15 - Average Forward Current vs. Maximum Allowable Case Temperature, 70HFL Series

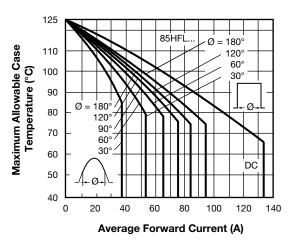


Fig. 16 - Average Forward Current vs. Maximum Allowable Case Temperature, 85HFL Series

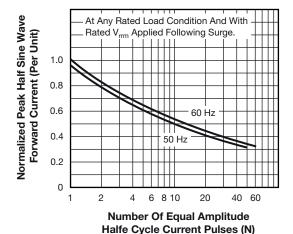


Fig. 17 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, All Series

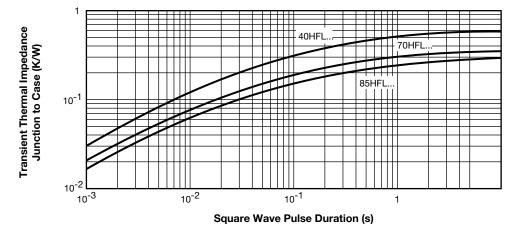


Fig. 18 - Maximum Transient Thermal Impedance, Junction to Case vs. Pulse Duration, All Series



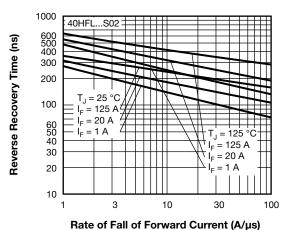


Fig. 19 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...S02 Series

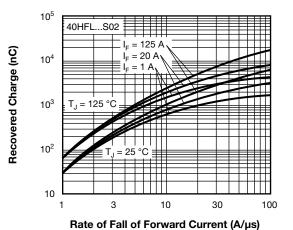


Fig. 20 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 40HFL...S02 Series

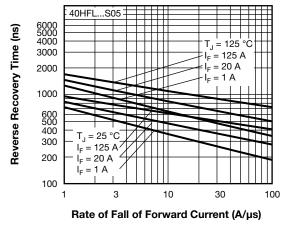


Fig. 21 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...S05 Series

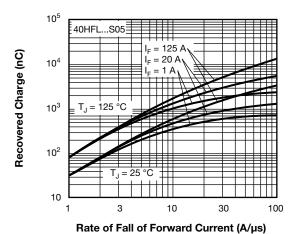


Fig. 22 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 40HFL...S05 Series

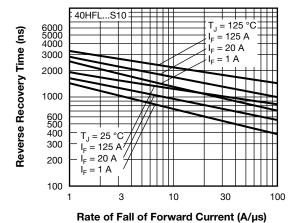


Fig. 23 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 40HFL...Series

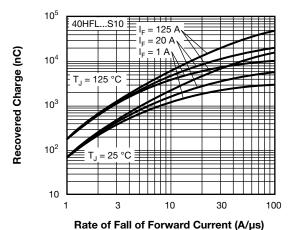


Fig. 24 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 40HFL...Series



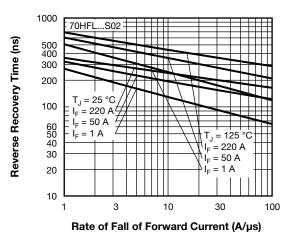


Fig. 25 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL...S02 Series

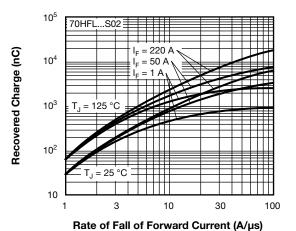


Fig. 26 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 70HFL...S02 Series

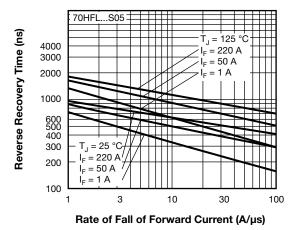


Fig. 27 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL...S05 Series

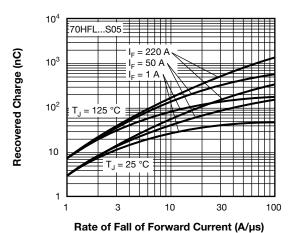


Fig. 28 - Typical Recovered Charge vs. Rate of Fall of Forward Current, 70HFL...S05 Series

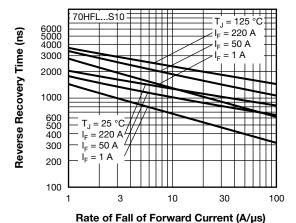


Fig. 29 - Typical Reverse Recovery Time vs. Rate of Fall of Forward Current, 70HFL... Series

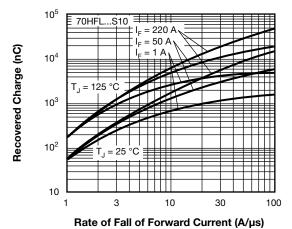
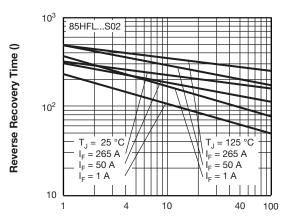


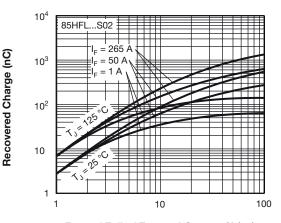
Fig. 30 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 70HFL... Series



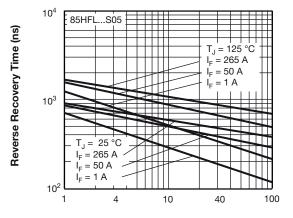




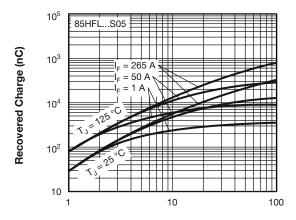
Rate of Fall of Forward Current (A/μs)
Fig. 31 - Typical Reverse Recovery Time vs.
Rate of Fall of Forward Current, 85HFL...S02 Series



Rate of Fall of Forward Current (A/μs)
Fig. 32 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 85HFL...S02 Series



Rate of Fall of Forward Current (A/μs)
Fig. 33 - Typical Reverse Recovery Time vs.
Rate of Fall of Forward Current, 85HFL...S05 Series



Rate of Fall of Forward Current (A/μs)
Fig. 34 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 85HFL...S05 Series

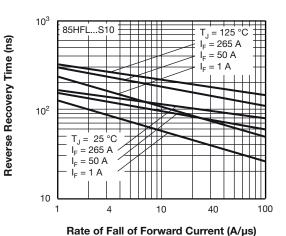
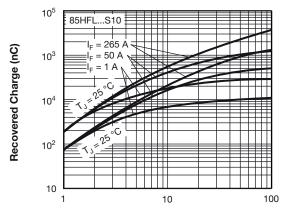


Fig. 35 - Typical Reverse Recovery Time vs.
Rate of Fall of Forward Current, 85HFL... Series

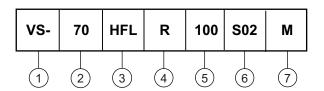


Rate of Fall of Forward Current (A/µs)
Fig. 36 - Typical Recovered Charge vs.
Rate of Fall of Forward Current, 85HFL... Series

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - • 70 = standard device (current rating: 40 = 40 A, 70 = 70 A, 85 = 85 A)

• 71 = not isolated lead

• 72, 87 = isolated lead with silicone sleeve

(red = reverse polarity)
(blue = normal polarity)

3 - HFL = fast recovery diode

- • None = stud normal polarity (cathode to stud)

• R = stud reverse polarity (anode to stud)

- Voltage code x 10 = V<sub>RRM</sub> (see "Voltage Ratings" table)

6 - Refer to "Recovery Characteristics" table

7 - • None = stud base DO-5 (DO-203AB) 1/4" 28UNF-2A

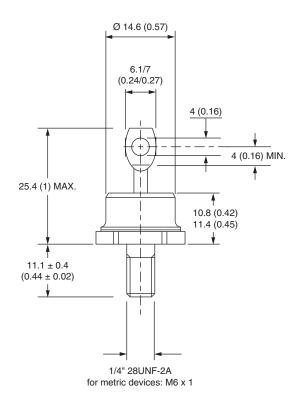
• M = stud base DO-5 (DO-203AB) M6 x 1

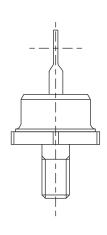
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95312			

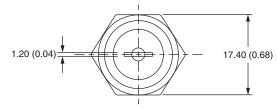


# DO-203AB (DO-5) for 40HFL, 70HFL and 85HFL

#### **DIMENSIONS FOR 40HFL/70HFL** in millimeters (inches)



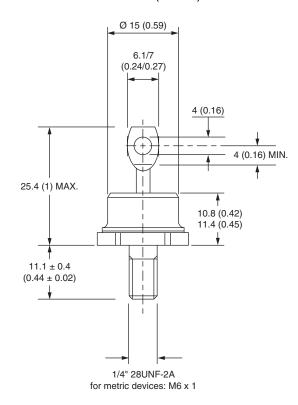


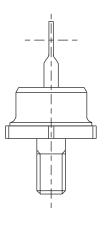


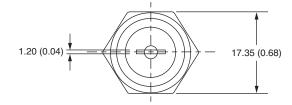
DO-203AB (DO-5) for 40HFL, 70HFL and 85HFL



#### **DIMENSIONS FOR 85HFL** in millimeters (inches)









#### **Legal Disclaimer Notice**

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